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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	HC08
Core Size	8-Bit
Speed	8MHz
Connectivity	-
Peripherals	LVD, POR, PWM
Number of I/O	5
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 4x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	16-SOIC (0.295", 7.50mm Width)
Supplier Device Package	16-SOIC
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc908qy4mdwer

Chapter 12
Input/Output Ports (PORTS)

Chapter 13
System Integration Module (SIM)

Chapter 2
Memory

2.1 Introduction

The central processor unit (CPU08) can address 64 Kbytes of memory space. The memory map, shown in Figure 2-1, includes:

- 4096 bytes of user FLASH for MC68HC908QT4 and MC68HC908QY4
- 1536 bytes of user FLASH for MC68HC908QT2, MC68HC908QT1, MC68HC908QY2, and MC68HC908QY1
- 128 bytes of random access memory (RAM)
- 48 bytes of user-defined vectors, located in FLASH
- 416 bytes of monitor read-only memory (ROM)
- 1536 bytes of FLASH program and erase routines, located in ROM

2.2 Unimplemented Memory Locations

Accessing an unimplemented location can have unpredictable effects on MCU operation. In Figure 2-1 and in register figures in this document, unimplemented locations are shaded.

2.3 Reserved Memory Locations

Accessing a reserved location can have unpredictable effects on MCU operation. In Figure 2-1 and in register figures in this document, reserved locations are marked with the word Reserved or with the letter R.

CHxMAX — Channel x Maximum Duty Cycle Bit

When the TOVx bit is at a 1, setting the CHxMAX bit forces the duty cycle of buffered and unbuffered PWM signals to 100%. As Figure 14-8 shows, the CHxMAX bit takes effect in the cycle after it is set or cleared. The output stays at the 100% duty cycle level until the cycle after CHxMAX is cleared.

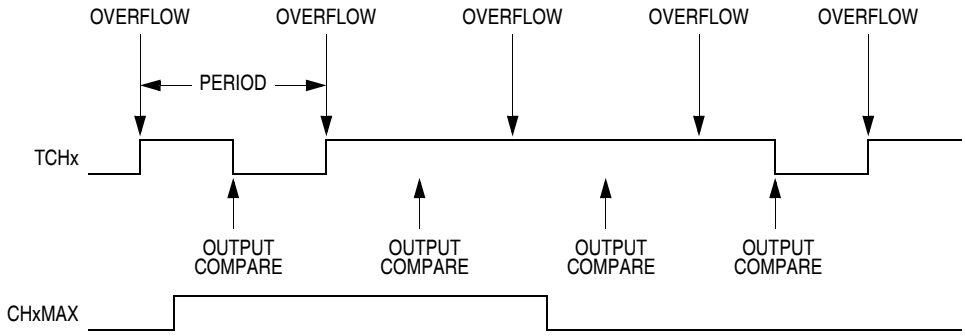

Figure 14-8. CHxMAX Latency

14.9.5 TIM Channel Registers

These read/write registers contain the captured TIM counter value of the input capture function or the output compare value of the output compare function. The state of the TIM channel registers after reset is unknown.

In input capture mode (MSxB:MSxA = 0:0), reading the high byte of the TIM channel x registers (TCHxH) inhibits input captures until the low byte (TCHxL) is read.

In output compare mode (MSxB:MSxA z0:0), writing to the high byte of the TIM channel x registers (TCHxH) inhibits output compares until the low byte (TCHxL) is written.

Address: $0026 TCH0H

	Bit 7	6	5	4	3	2	1	Bit 0
Read: Write:	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8
Reset:	Indeterminate after reset							

Address: $0027 TCH0L

	Bit 7	6	5	4	3	2	1	Bit 0
Read: Write:	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Reset:	Indeterminate after reset							

Address: $0029 TCH1H

	Bit 7	6	5	4	3	2	1	Bit 0
Read: Write:	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8
Reset:	Indeterminate after reset							

Address: $02A TCH1L

	Bit 7	6	5	4	3	2	1	Bit 0
Read: Write:	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Reset:	Indeterminate after reset							

Figure 14-9. TIM Channel Registers (TCH0H/L:TCH1H/L)

15.2.2.1 Break Status and Control Register

The break status and control register (BRKSCR) contains break module enable and status bits.

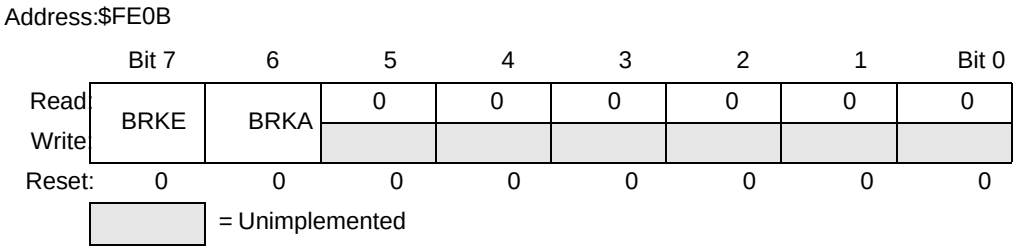

Figure 15-3. Break Status and Control Register (BRKSCR)

BRKE — Break Enable Bit

This read/write bit enables breaks on break address register matches. Clear BRKE by writing a 0 to bit 7. Reset clears the BRKE bit.

1 = Breaks enabled on 16-bit address match
0 = Breaks disabled

BRKA — Break Active Bit

This read/write status and control bit is set when a break address match occurs. Writing a 1 to BRKA generates a break interrupt. Clear BRKA by writing a 0 to it before exiting the break routine. Reset clears the BRKA bit.

1 = Break address match
0 = No break address match

15.2.2.2 Break Address Registers

The break address registers (BRKH and BRKL) contain the high and low bytes of the desired breakpoint address. Reset clears the break address registers.

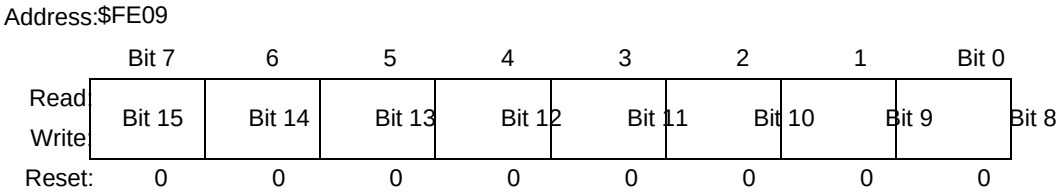

Figure 15-4. Break Address Register High (BRKH)

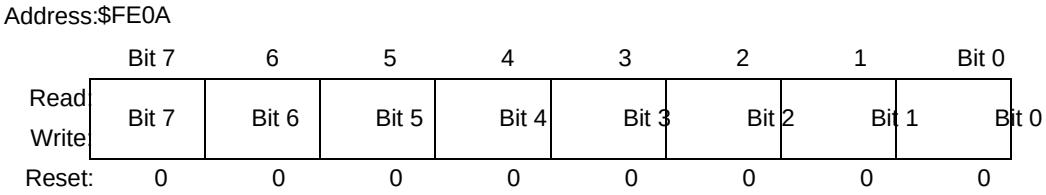

Figure 15-5. Break Address Register Low (BRKL)

15.3.1 Functional Description

Figure 15-9 shows a simplified diagram of monitor mode entry.

The monitor module receives and executes commands from a host computer. Figure 15-10, Figure 15-11, and Figure 15-12 show example circuits used to enter monitor mode and communicate with a host computer via a standard RS-232 interface.

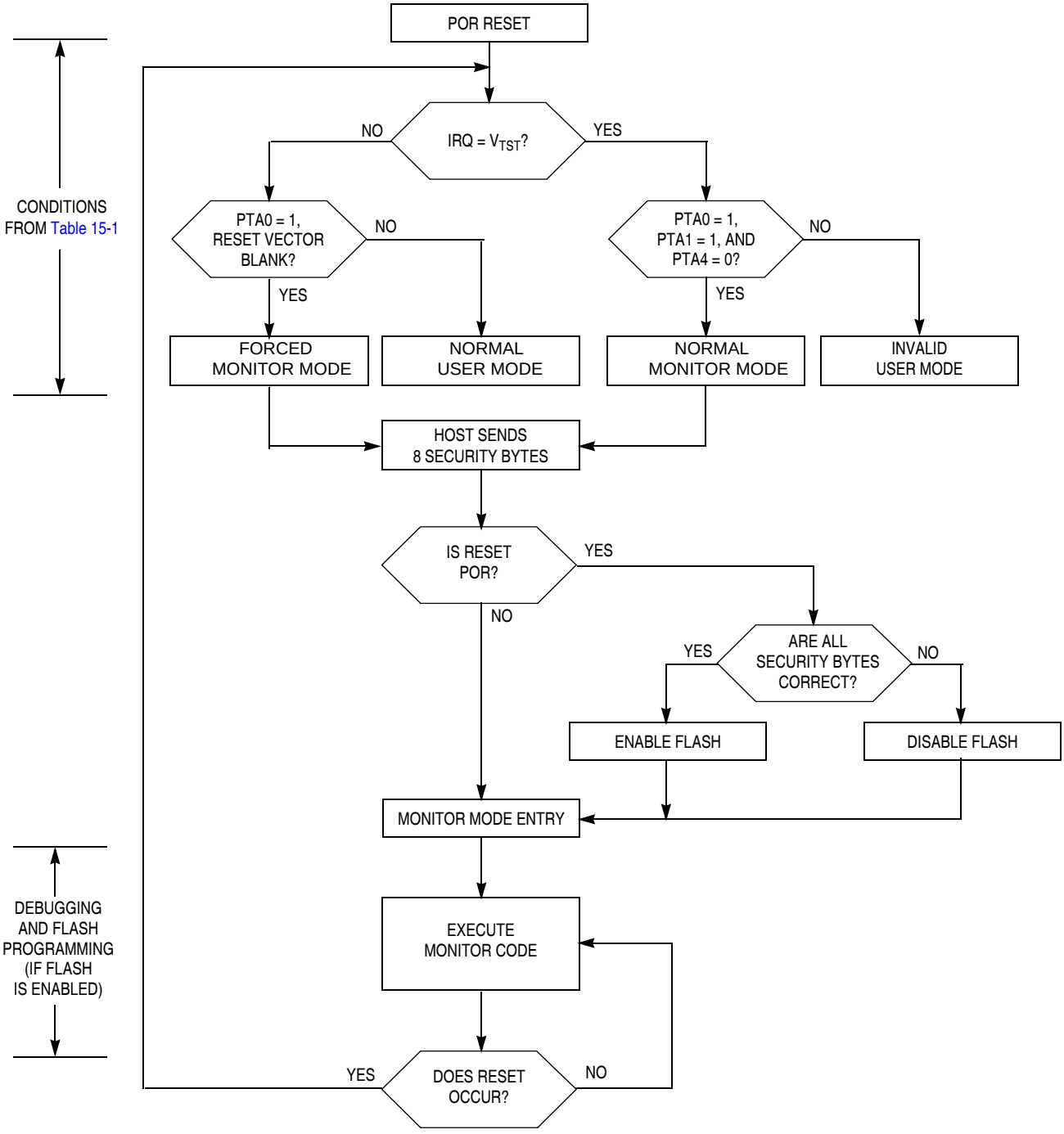

Figure 15-9. Simplified Monitor Mode Entry Flowchart

16.11 3-V Control Timing

Characteristic[1]	Symbol	Min	Max	Unit
Internal operating frequency	f_{OP} (f_{Bus})	—	4	MHz
Internal clock period ($1/f_{OP}$)	t_{cyc}	250	—	ns
$\overline{RST}$ input pulse width low	t_{RL}	200	—	ns
$\overline{IRQ}$ interrupt pulse width low (edge-triggered)	t_{ILIH}	200	—	ns
$\overline{IRQ}$ interrupt pulse period	t_{ILIL}	Note[2]	—	t_{cyc}

1. V_{DD} = 2.7 to 3.3 Vdc, V_{SS} = 0 Vdc, $T_A = T_L$ to T_H; timing shown with respect to 20% V_{DD} and 70% V_{DD}, unless otherwise noted.
2. The minimum period is the number of cycles it takes to execute the interrupt service routine plus 1 t_{cyc}.

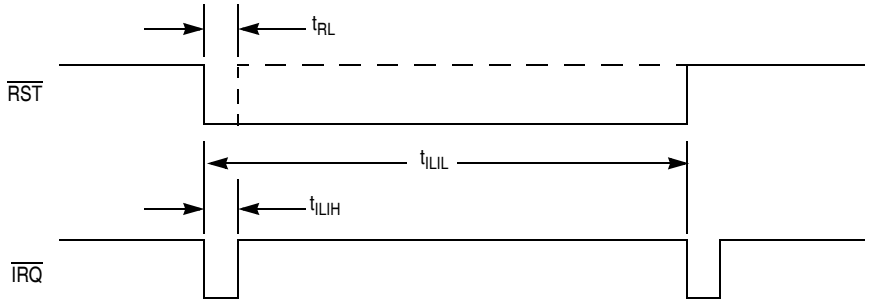

Figure 16-7. $\overline{RST}$ and $\overline{IRQ}$ Timing

16.16 Memory Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
RAM data retention voltage	V_{RDR}	1.3	—	—	V
FLASH program bus clock frequency	—	1	—	—	MHz
FLASH read bus clock frequency	f_{Read}(1)	0	—	8 M	Hz
FLASH page erase time <1 k cycles >1 k cycles	t_{Erase}	 0.9 3.6	 1 4	 1.1 5.5	ms
FLASH mass erase time	t_{MErase}	4	—	—	ms
FLASH PGM/ERASE to HVEN setup time	t_{NVS}	10	—	—	μs
FLASH high-voltage hold time	t_{NVH}	5	—	—	μs
FLASH high-voltage hold time (mass erase)	t_{NVHL}	100	—	—	μs
FLASH program hold time	t_{PGS}	5	—	—	μs
FLASH program time	t_{PROG}	30	—	40	μs
FLASH return to read time	t_{RCV}(2)	1	—	—	μs
FLASH cumulative program HV period	t_{HV}(3)	—	—	4	ms
FLASH endurance(4)	—	10 k	100 k	—	Cycles
FLASH data retention time(5)	—	15	100	—	Years

1. f_{Read} is defined as the frequency range for which the FLASH memory can be read.
2. t_{RCV} is defined as the time it needs before the FLASH can be read after turning off the high voltage charge pump, by clearing HVEN to 0.
3. t_{HV} is defined as the cumulative high voltage programming time to the same row before next erase. t_{HV} must satisfy this condition: $t_{NVS} + t_{NVH} + t_{PGS} + (t_{PROG} \times 32)$ dt_{HV} maximum.
4. Typical endurance was evaluated for this product family. For additional information on how Freescale defines Typical Endurance, please refer to Engineering Bulletin EB619.
5. Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25•C using the Arrhenius equation. For additional information on how Freescale defines Typical Data Retention, please refer to Engineering Bulletin EB618.

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. DATUMS A AND B TO BE DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
4. THIS DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
5. THIS DIMENSION DOES NOT INCLUDE INTER–LEAD FLASH OR PROTRUSIONS. INTER–LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
6. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.62 mm.